Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	111914	semiconductor near laser	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/19 16:11
S2	14949	facet and coat$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/11 23:11
S3	2965	S2 and S1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/19 17:11
S4	65	(facet with (si$N$H))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/11 23:12
S5	65	(facet$2 with (si$N$H))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/11 23:12
S6	11	(facet$2 with (si$N$H)) and S1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/11 23:45
S7	2	("6541164").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/11 23:21
S8	2	("6432620").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/11 23:21
S9	0	"si.sub.1.N.sub.$1.H.sub.1"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/11 23:46

S10	48370	Si$1N$1H1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/11 23:47
S11	835	S10 and S1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/11 23:47
S12	323	(Si$1N$1H1 with (facet$2 coat$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/11 23:49
S13	158	(Si$1N$1H1 with (facet$2 coat$4)) and @ad <"20011106"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/12 00:07
S14	13	(Si$1N$1H1 with (facet$2 coat$4)) and @ad <"20011106" and S1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/11 23:51
S15	37	(Si$1N$1H1 with (facet$2 coat$4)) and @ad <"20011106" and laser	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/19 16:55
S16	24	S15 not S14	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/11 23:58
S17	46	(Si$1N$1H1 with (facet$2 coat$4)) and @ad <"20011106" and amorphous	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/12 00:08
S18	1	(Si$1N$1H1 with (facet$2 coat$4)) and @ad <"20011106" and (amorphous with Si$1N$1H1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/12 00:09
S19	3	(Si$1N$1H1 with (facet$2 coat$4)) and @ad <"20011106" and (amorphous same Si$1N$1H1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/12 00:10

S20	46	(Si$1N$1H1 with (facet$2 coat$4)) and @ad <"20011106" and amorphous	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/12 00:10
S21	2	("20040151226").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/19 16:11
S22	2373	Ga$As and Ga$al$as and (facet$2 coat$4) and @ad <"20011106" and laser	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/19 17:12
S23	38892	("372").CLAS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/19 16:57
S24	1025	S22 and S23	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/19 16:57
S25	704	S22 and S23 and wavelength and (semiconductor near laser)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/19 16:57
S26	182	facet with si$2N	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/19 17:12
S27	64	facet with si$2N and (semiconductor near laser)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/19 17:12
S28	43	facet with si$2N and (semiconductor near laser) and @ad <"20011106"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/19 17:12
S29	43	(facet with si$2N) and (semiconductor near laser) and @ad <"20011106"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/19 17:28

S30	54	(facet with amorphous) and (semiconductor near laser) and @ad <"20011106"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/19 21:07
S31	15	(facet with amorphous) and (semiconductor near laser) and @ad <"20011106" and (nitrogen nitro)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/19 21:12
S32	22	(facet with amorphous) and (semiconductor near laser) and @ad <"20011106" and (nitrogen nitro nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/19 22:01
S33	12	(facet with amorphous) and (semiconductor near laser) and @ad <"20011106" and (nitrogen nitro nitride) and Ga$As and Ga$al$as	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/19 21:13
S34	3	("4280107" | "5892786" | "RE37354").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/19 22:00
S35	16	(facet with amorphous) and (semiconductor near laser) and @ad <"20011106" and (nitrogen nitro nitride) and (ratio with (Si and H)(silicon and hydrogen))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/19 22:02
S36	2	(facet with amorphous) and (semiconductor near laser) and @ad <"20011106" and (nitrogen nitro nitride) and (ratio with ((Si and H)(silicon and hydrogen)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/19 22:02